IN THE CLAIMS:

Please amend the claims as follows:

1. Field-effect power transistor having:

   (a) a first semiconductor region ~~(10)~~ with first MOS channels ~~(20)~~ having a first ratio of a channel width ~~(w)~~ to a channel length ~~(l)~~ for conducting through an electric current from a source terminal ~~(17)~~ to a drain terminal ~~(11)~~ in a manner dependent on a signal at a gate contact ~~(10')~~ of the first semiconductor region ~~(10)~~;

   (b) at least one second semiconductor region ~~(12)~~ with second MOS channels ~~(22)~~ having a second ratio of the channel width ~~(w)~~ to the channel length ~~(l)~~ for conducting through an electric current from the source terminal ~~(17)~~ to the drain terminal ~~(11)~~ in a manner dependent on a signal at the gate contact ~~(12')~~ of the second semiconductor region ~~(12)~~; ~~and~~

   (c) a drive terminal ~~(16)~~ for providing a drive signal at the gate contacts ~~(10'; 12')~~, a first predetermined resistor ~~(14)~~ in each case being provided between the gate contact ~~(12')~~ of the at least second semiconductor region ~~(12)~~ and the drive terminal ~~(16)~~; and

   (d) an overvoltage protection device ~~(13)~~ being provided at least between the gate contact ~~(12')~~ of the second semiconductor region ~~(12)~~ and the drain terminal ~~(11)~~, said device switching on the at least second semiconductor region ~~(12)~~ if the voltage between the gate contact ~~(12')~~ of the second semiconductor region ~~(12)~~ and the drain terminal ~~(11)~~ exceeds a predetermined value.

2. Power semiconductor according to claim 1, ~~characterized in that~~ wherein the second ratio of the channel width ~~(w)~~ to the channel length ~~(l)~~ is less than or approximately equal to the first ratio of the channel width ~~(w)~~ to the channel length ~~(l)~~.

3. Power semiconductor according to claim 2, ~~characterized in that~~ wherein the second ratio of the channel width ~~(w)~~ to the channel length ~~(l)~~ is at least a factor of 2 less than the first ratio of the channel width ~~(w)~~ to the channel length ~~(l)~~.

4. Power semiconductor according to ~~one of the preceding claims, characterized in that~~ claim 1, wherein the first semiconductor region ~~(10)~~ and the second semiconductor region ~~(12)~~ intermesh, preferably in finger-like fashion.

5. Power semiconductor according to ~~one of the preceding claims, characterized in that~~ claim 1, wherein the first semiconductor region ~~(10)~~ is formed by the first channels ~~(20)~~, which are connected to the gate terminal ~~(16)~~ of the field-effect power transistor, and the second semiconductor region ~~(12)~~ is formed by the second channels ~~(22)~~, which lie between the first channels ~~(20)~~ and are connected to the overvoltage protection device ~~(13)~~.

6. Power semiconductor according to ~~one of the preceding claims, characterized in that~~ claim 1, wherein the overvoltage protection device ~~(13)~~ is provided in the form of a zener diode.

7. Power semiconductor according to ~~one of the preceding claims, characterized in that~~ claim 1, wherein the second channels ~~(22)~~ are provided in strip-like fashion laterally separated by first channels ~~(20)~~, preferably equidistantly.

8. Power semiconductor according to ~~one of the preceding claims, characterized in that~~ claim 1, wherein the first and second channels ~~(20; 22)~~ are patterned in the same way and/or embodied as trenches.

9. Power semiconductor according to claim 8, ~~characterized in that~~ wherein the trenches ~~(20; 22)~~ are embodied with uniform oxide thickness.

10. Power semiconductor according to claim 8, ~~characterized in that~~ wherein the trenches ~~(20; 22)~~ are embodied as field plate trenches.

11. Power semiconductor according to ~~one of the preceding claims, characterized in that~~ claim 1, wherein the first predetermined resistor ~~(14)~~ is embodied between the two gate contacts ~~(10'; 12')~~ as a polysilicon resistor.

12. Power semiconductor according to ~~one of the preceding claims, characterized in that~~ claim 1, wherein the first predetermined resistor ~~(14)~~ is embodied between the two gate contacts ~~(10'; 12')~~ as a trench poly-resistor, adjustable by way of the trench length, trench width and number of trenches.

13. Power semiconductor according to ~~one of the preceding claims, characterized in that~~ claim 1, wherein the first predetermined resistor ~~(14)~~ is embodied as a semiconductor region with a predetermined dopant concentration.

14. Power semiconductor according to ~~one of the preceding claims, characterized in that~~ claim 1, wherein the value of the first predetermined resistor ~~(14)~~ is dimensioned in a manner dependent on a gate resistor ~~(15)~~.

15. Power semiconductor according to claim 14, ~~characterized in that~~ wherein the value of the first predetermined resistor ~~(14)~~ lies in the range between 0.2 and 2 times the value of the gate resistor ~~(15)~~, preferably between half the value of said gate resistor and the value of said gate resistor.

16. Power semiconductor according to ~~one of the preceding claims, characterized in that~~ claim 1, wherein a second predetermined resistor ~~(18)~~ is provided between the drive terminal ~~(16)~~ and the gate contact ~~(10')~~ of the first semiconductor region ~~(10)~~.

17. Power semiconductor according to claim 16, ~~characterized in that~~ wherein the second predetermined resistor ~~(18)~~ is dimensioned in a manner dependent on the first predetermined resistor ~~(14)~~ and the gate capacitances of the respectively adjoining gate contacts ~~(10'; 12')~~.

18. Power semiconductor according to claim 16, ~~characterized in that~~ wherein the second predetermined resistor ~~(18)~~ is dimensioned in such a way that the product of the first predetermined resistor ~~(14)~~ and the gate capacitance of the second semiconductor region ~~(12)~~ is approximately equal to the product of the second predetermined resistor ~~(18)~~ and the gate capacitance of the first semiconductor region ~~(10)~~.